

PATENT ABSTRACTS OF JAPAN

(11)Publication number : 10-189951
 (43)Date of publication of application : 21.07.1998

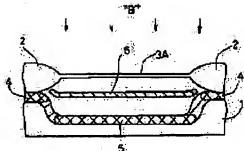
(51)Int.Cl. H01L 29/78

(21)Application number : 08-348676 (71)Applicant : SANYO ELECTRIC CO LTD
 (22)Date of filing : 26.12.1996 (72)Inventor : OKABE YUUSHIROU

(54) MANUFACTURE OF SEMICONDUCTOR DEVICE**(57)Abstract:**

PROBLEM TO BE SOLVED: To attain a high threshold voltage with low ion implantation, without causing degradation of isolation characteristic.

SOLUTION: Boron ions ($11B^+$) are implanted under conditions for penetrating an LOCOS oxide 2 deposited on a P-type silicon substrate 1, in order to form a channel stopper layer 4 beneath the LOCOS oxide 2 of the same time as with a first channel ion implantation layer 5 in a deep region within the substrate 1. Subsequently, boron ions ($11B^+$) are implanted from above the substrate 1 under conditions of not penetrating the LOCOS oxide 2, in order to form a second channel ion implantation layer 6 beneath a region for forming a diffusion layer in the substrate which is shallower than the first channel ion implantation layer 5.

**LEGAL STATUS**

[Date of request for examination] 22.02.2001

[Date of sending the examiner's decision of rejection] 03.12.2002

[Kind of final disposal of application other than the examiner's decision of rejection or application converted registration]

[Date of final disposal for application]

[Patent number]

[Date of registration]

[Number of appeal against examiner's decision of rejection]

[Date of requesting appeal against examiner's decision of rejection]

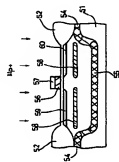
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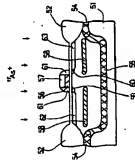
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【図12】



【図13】



【図14】

